
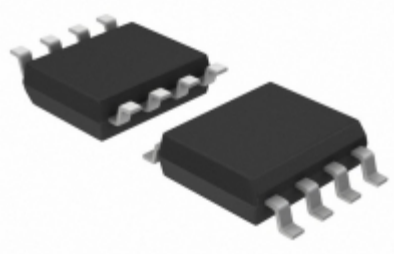





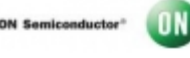

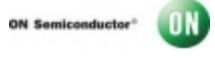
	<h2 style="color: #E67E22;">NTMS4807NR2G</h2>
	<p>Hersteller-Teilenummer: NTMS4807NR2G</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 9.1A 8-SOIC</p> <p>Datenblätter:  NTMS4807NR2G.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 41097 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	NTMS4807NR2G
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 30V 9.1A 8-SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	41097 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SOIC
Verlustleistung (max)	860mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	9.1A (Ta)
Rds On (Max) @ Id, Vgs	6.1 mOhm @ 14.8A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	24nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	2900pF @ 24V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)



















































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Sie können auch interessiert sein:

 <p>NTMS4801NR2G AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 7.5A 8-SOIC</p>	 <p>NTMS4802NR2G AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 11.1A 8-SOIC</p>	 <p>NTMS4840NR2G AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 4.5A 8SOIC</p>	 <p>NTMS4816NG ON NTMS4816NG ON</p>
 <p>NTMS4872NR2G AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 6A 8-SOIC</p>	 <p>NTMS4816N AMI Semiconductor / ON Semiconductor NTMS4816N ON</p>	 <p>NTMS4807NR ON NTMS4807NR ON</p>	 <p>NTMS4802N AMI Semiconductor / ON Semiconductor NTMS4802N ON</p>

heiße Teile

Mehr

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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